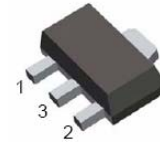
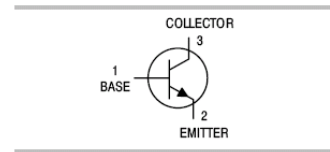


NPN Silicon AF Transistors

BCX54/BCX55/BCX56

FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types:BCX51...BCX53(PNP)



SOT-89

ORDERING INFORMATION

Type No.	Marking	Package Code
BCX54	BA	SOT-89
BCX54-10	BC	SOT-89
BCX54-16	BD	SOT-89
BCX55	BE	SOT-89
BCX55-10	BG	SOT-89
BCX55-16	BM	SOT-89
BCX56	BH	SOT-89
BCX56-10	BK	SOT-89
BCX56-16	BL	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BCX54	45
		BCX55	60
		BCX56	100
V_{CEO}	Collector-Emitter Voltage	BCX54	45
		BCX55	60
		BCX56	80
V_{EBO}	Emitter-Base Voltage	5	V
I_C	DC Collector Current	1	A
I_{CM}	Peak Collector Current	1.5	A
I_B	Base current	100	mA
I_{BM}	Peak base current	200	mA
P_{tot}	Total power dissipation, $T_S=130^\circ\text{C}$	1	W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C

NPN Silicon AF Transistors

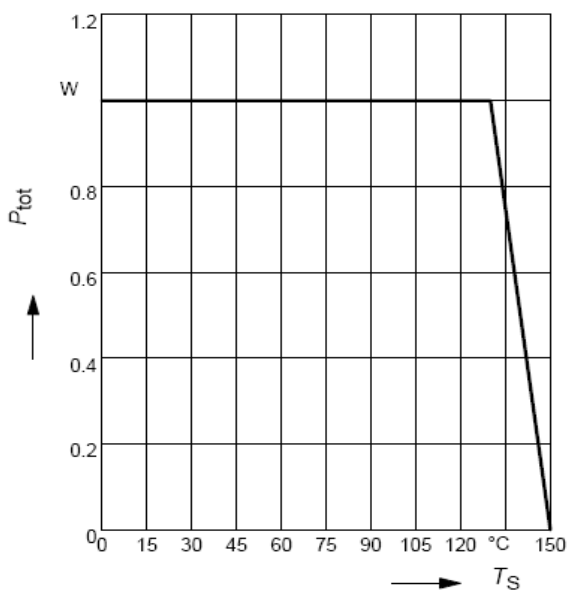
BCX54/BCX55/BCX56

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ $I_B=0$ BCX54 BCX55 BCX56	45 60 100		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}$ $I_B=0$ BCX54 BCX55 BCX56	45 60 80		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$ $I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}$ $I_E=0$		100	nA
		$V_{CB}=30\text{V}$ $I_E=0$, $T_A=150^\circ\text{C}$		20	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}$ $I_C=5\text{mA}$	25		
		$V_{CE}=2\text{V}$ $I_C=150\text{mA}$	40	250	
		$V_{CE}=2\text{V}$ $I_C=500\text{mA}$	25		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}$ $I_B=50\text{mA}$		0.5	V
Base-emitter voltage	V_{BE}	$I_C=500\text{mA}$, $V_{CE}=2\text{V}$		1	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$, $f=20\text{MHz}$	100		MHz

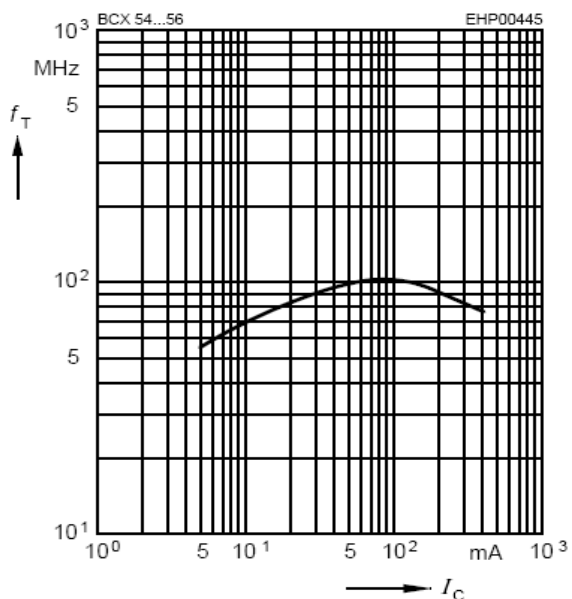
TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

Total power dissipation $P_{tot} = f(T_S)$



Transition frequency $f_T = f(I_C)$

$V_{CE} = 10\text{V}$

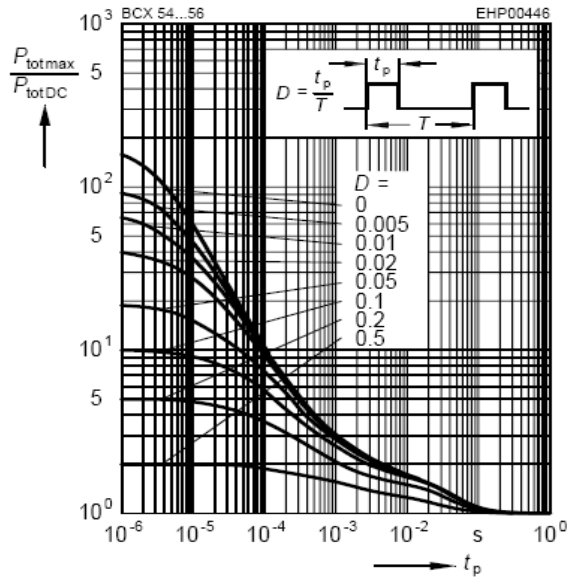


NPN Silicon AF Transistors

BCX54/BCX55/BCX56

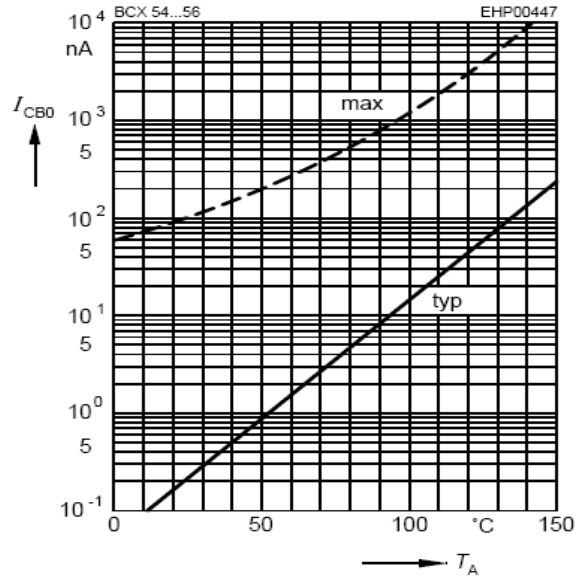
Permissible pulse load

$$P_{totmax} / P_{totDC} = f(t_p)$$



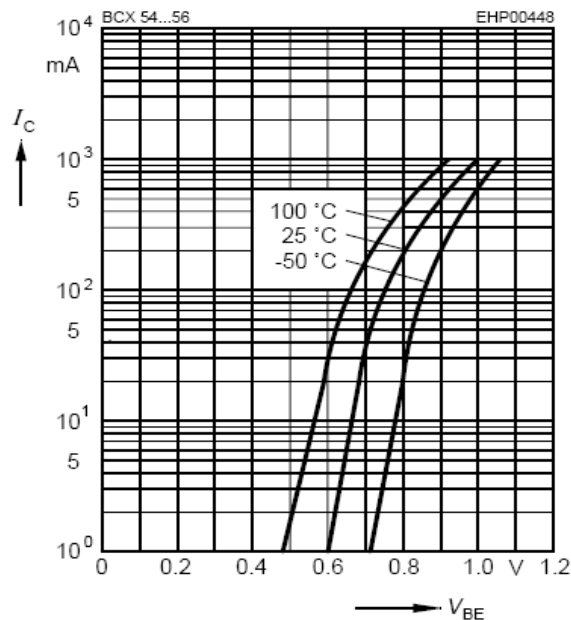
Collector cutoff current $I_{CBO} = f(T_A)$

$$V_{CB} = 30V$$



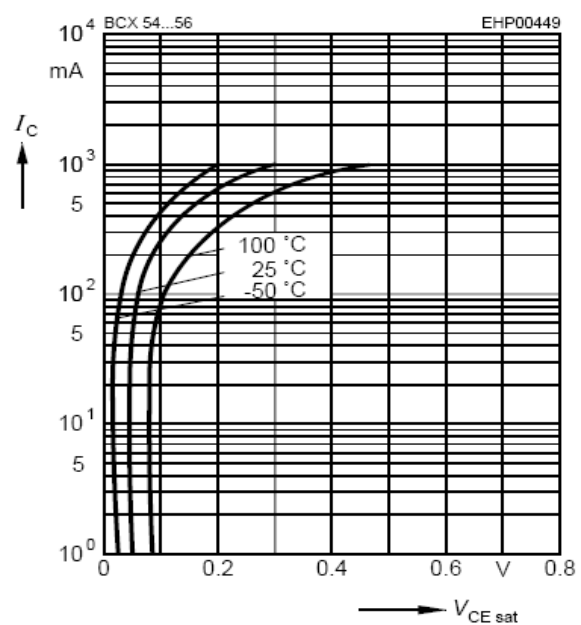
Collector current $I_C = f(V_{BE})$

$$V_{CE} = 2V$$



Collector-emitter saturation voltage

$$I_C = f(V_{CEsat}), h_{FE} = 10$$



NPN Silicon AF Transistors

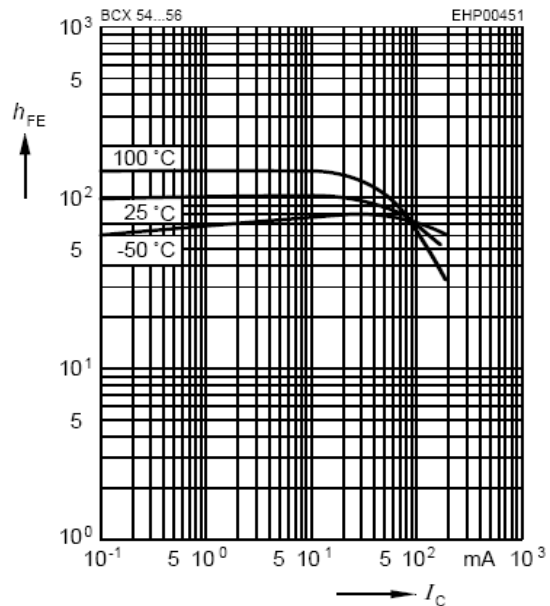
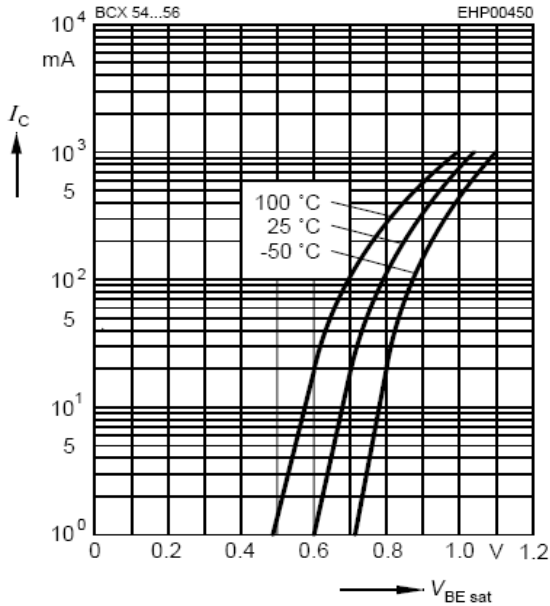
BCX54/BCX55/BCX56

Base-emitter saturation voltage

$$I_C = f(V_{BEsat}), h_{FE} = 10$$

DC current gain $h_{FE} = f(I_C)$

$$V_{CE} = 2V$$



PACKAGE OUTLINE

Plastic surface mounted package

SOT-89

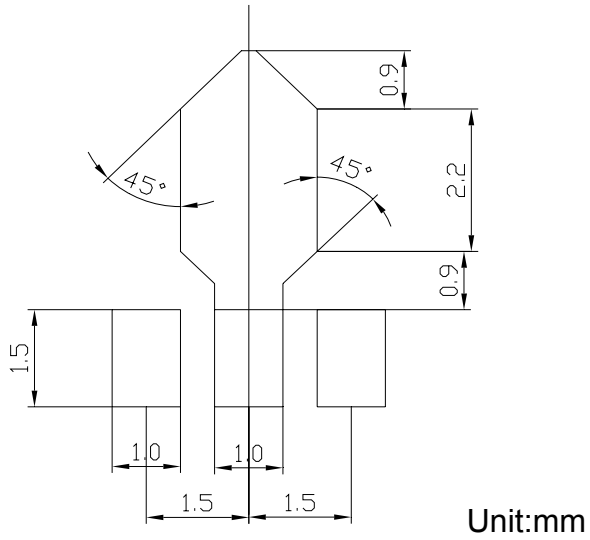
Mechanical drawing of the SOT-89 package showing dimensions A, B, C, D, E, F, H, J, and K. The drawing includes a top view, a side view, and a bottom view.

SOT-89		
Dim	Min	Max
A	4.5	4.7
B	2.3	2.7
C	1.5Typical	
D	0.35	0.55
E	1.4	1.6
F	0.4	0.6
H	1.55	1.75
J	0.4Typical	
K	4.15	4.25
All Dimensions in mm		

NPN Silicon AF Transistors

BCX54/BCX55/BCX56

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BCX54/BCX55/BCX56	SOT-89	1000/Tape&Reel